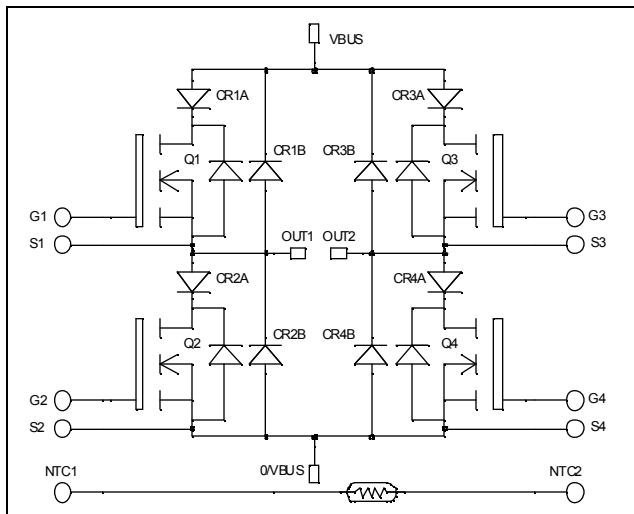


**Full - Bridge
Series & SiC parallel diodes
Super Junction
MOSFET Power Module**



$V_{DSS} = 600V$

$R_{DSon} = 70m\Omega \text{ max @ } T_j = 25^\circ C$

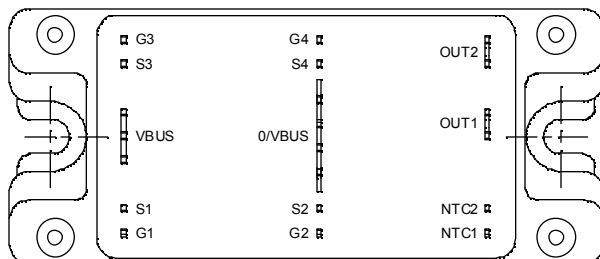
$I_D = 39A \text{ @ } T_c = 25^\circ C$

Application

- Motor control
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- **COOLMOS** Power Semiconductors
 - Ultra low R_{DSon}
 - Low Miller capacitance
 - Ultra low gate charge
 - Avalanche energy rated
- **Parallel SiC Schottky Diode**
 - Zero reverse recovery
 - Zero forward recovery
 - Temperature Independent switching behavior
 - Positive temperature coefficient on VF
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- Internal thermistor for temperature monitoring
- High level of integration



Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS complaint

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	600	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	39
		$T_c = 80^\circ C$	29
I_{DM}	Pulsed Drain current	156	A
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	70	$m\Omega$
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	250
I_{AR}	Avalanche current (repetitive and non repetitive)	20	A
E_{AR}	Repetitive Avalanche Energy	1	mJ
E_{AS}	Single Pulse Avalanche Energy	1800	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0\text{V}, V_{DS} = 600\text{V}$	$T_j = 25^\circ\text{C}$			250	μA
		$V_{GS} = 0\text{V}, V_{DS} = 600\text{V}$	$T_j = 125^\circ\text{C}$			500	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10\text{V}, I_D = 19.5\text{A}$				70	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 1\text{mA}$		2.1	3	3.9	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$				± 100	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}$			7015		pF
C_{oss}	Output Capacitance	$V_{DS} = 25\text{V}$			2565		
C_{rss}	Reverse Transfer Capacitance	$f = 1\text{MHz}$			212		
Q_g	Total gate Charge	$V_{GS} = 10\text{V}$			259		nC
Q_{gs}	Gate – Source Charge	$V_{Bus} = 300\text{V}$			29		
Q_{gd}	Gate – Drain Charge	$I_D = 39\text{A}$			111		
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @ 125°C $V_{GS} = 15\text{V}$ $V_{Bus} = 400\text{V}$ $I_D = 39\text{A}$ $R_G = 5\Omega$			21		ns
T_r	Rise Time				30		
$T_{d(off)}$	Turn-off Delay Time				283		
T_f	Fall Time				84		
E_{on}	Turn-on Switching Energy	Inductive switching @ 25°C $V_{GS} = 15\text{V}, V_{Bus} = 400\text{V}$ $I_D = 39\text{A}, R_G = 5\Omega$			402		μJ
E_{off}	Turn-off Switching Energy				980		
E_{on}	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 15\text{V}, V_{Bus} = 400\text{V}$ $I_D = 39\text{A}, R_G = 5\Omega$			657		μJ
E_{off}	Turn-off Switching Energy				1206		

Series diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			200			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 200\text{V}$	$T_j = 25^\circ\text{C}$			250	μA
			$T_j = 125^\circ\text{C}$			500	
I_F	DC Forward Current		$T_c = 85^\circ\text{C}$		30		A
V_F	Diode Forward Voltage	$I_F = 30\text{A}$			1.1	1.15	V
		$I_F = 60\text{A}$			1.4		
		$I_F = 30\text{A}$	$T_j = 125^\circ\text{C}$		0.9		
t_{rr}	Reverse Recovery Time	$I_F = 30\text{A}$ $V_R = 133\text{V}$ $di/dt = 200\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		24		ns
			$T_j = 125^\circ\text{C}$		48		
Q_{rr}	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$		33		nC
			$T_j = 125^\circ\text{C}$		150		

Parallel diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I _{RM}	Maximum Reverse Leakage Current	V _R =600V	T _j = 25°C		100	400	μA
			T _j = 175°C		200	2000	
I _F	DC Forward Current		T _c = 125°C		20		A
V _F	Diode Forward Voltage	I _F = 20 A	T _j = 25°C		1.6	1.8	V
			T _j = 175°C		2.0	2.4	
Q _C	Total Capacitive Charge	I _F = 20 A, V _R = 300 V di/dt = 800 A/μs			28		nC
C	Total Capacitance	f = 1 MHz, V _R = 200 V			130		pF
		f = 1 MHz, V _R = 400 V			100		

Thermal and package characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance	Transistor				0.5	°C/W
		Series diode				1.2	
		Parallel diode				1.5	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, I _{isol} < 1 mA, 50/60 Hz			2500			V
T _J	Operating junction temperature range			-40		150	°C
T _{STG}	Storage Temperature Range			-40		125	
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To Heatsink	M5	1.5		4.7	N.m
Wt	Package Weight					160	g

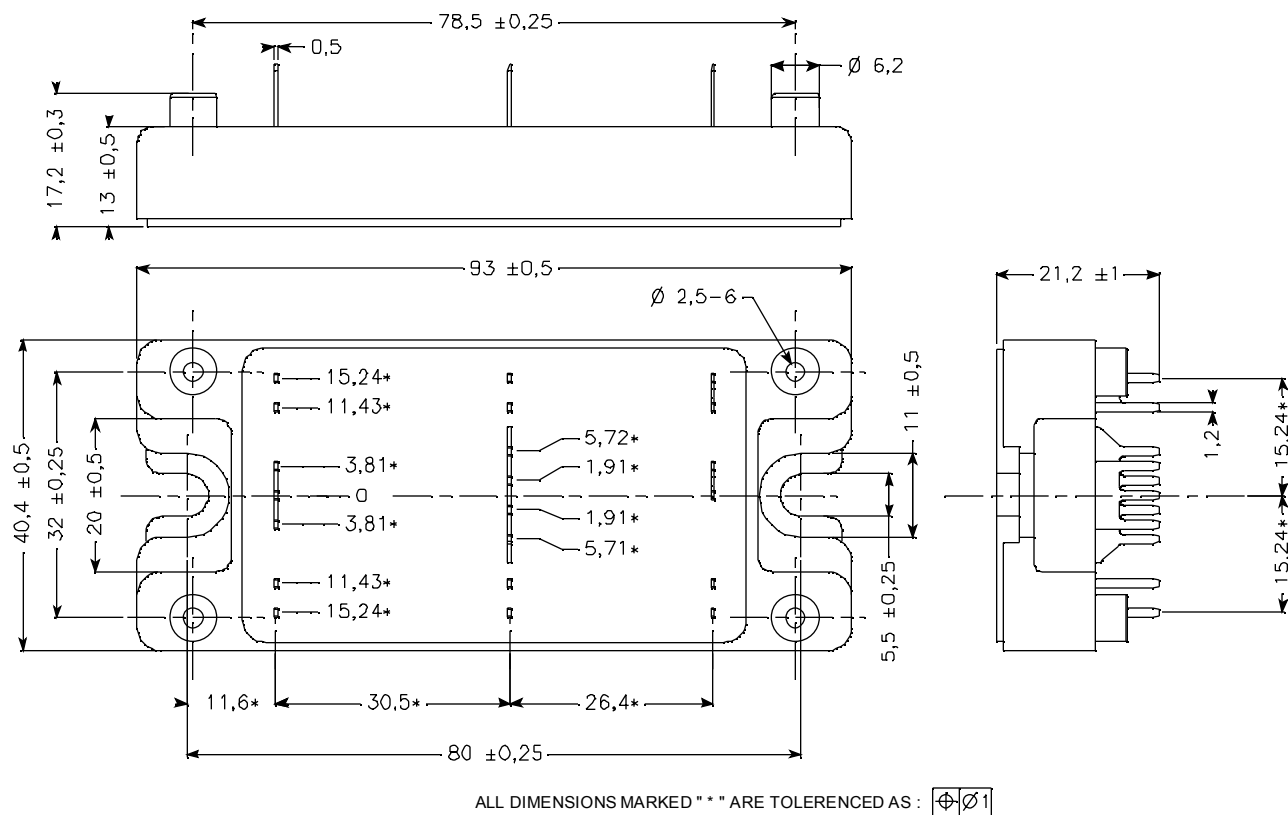
Temperature sensor NTC (see application note APT0406 on www.advancedpower.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B _{25/85}	T ₂₅ = 298.15 K		3952		K

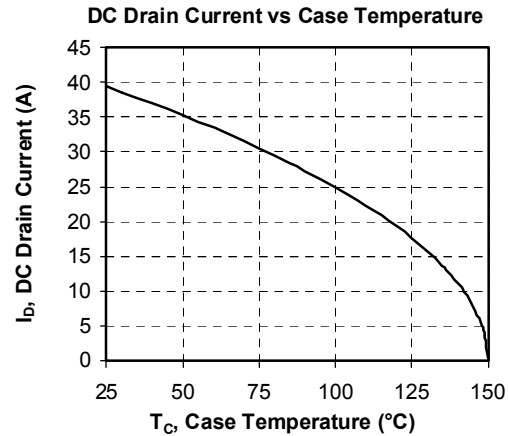
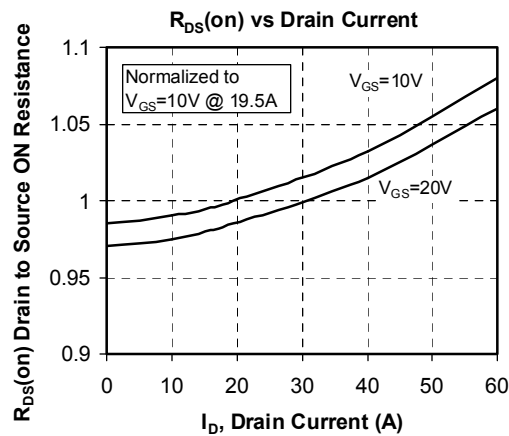
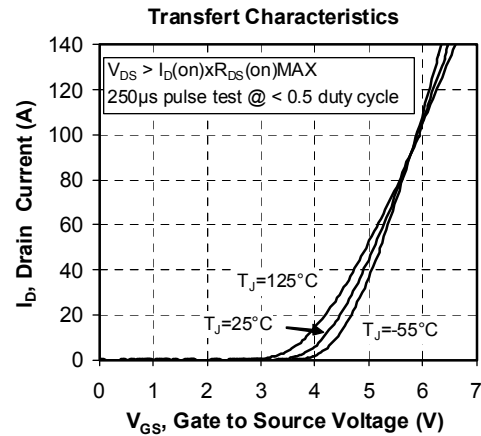
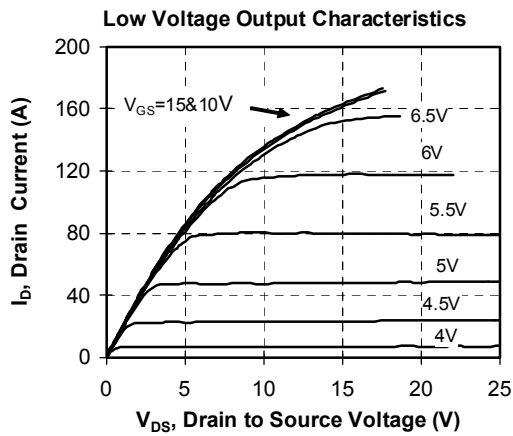
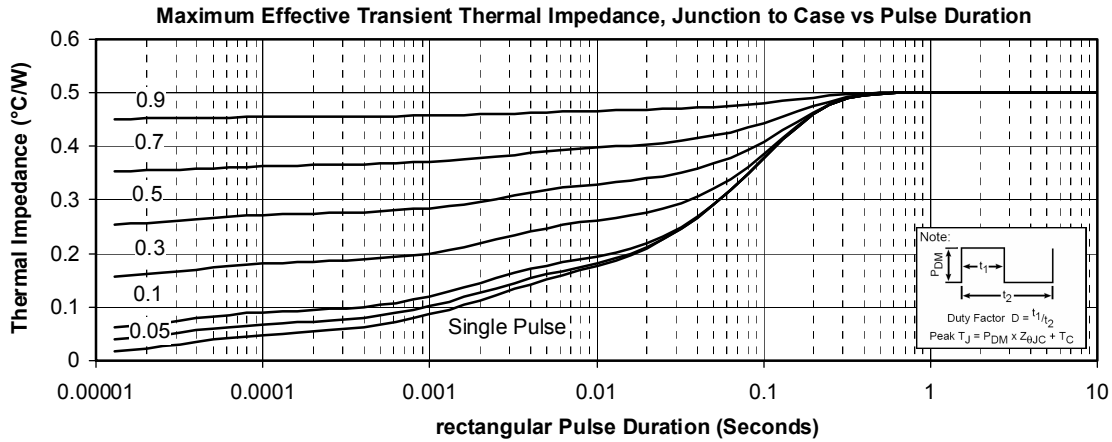
$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

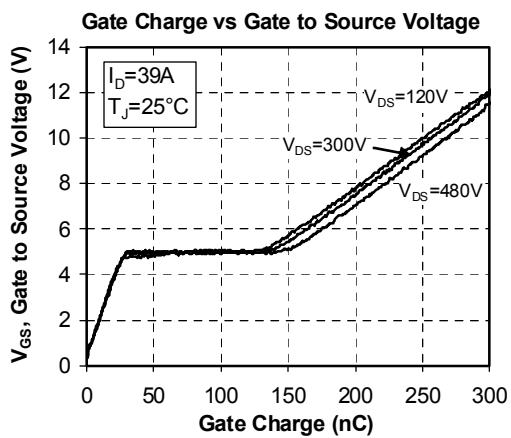
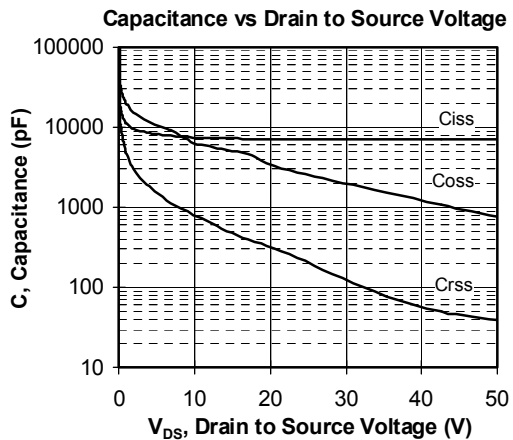
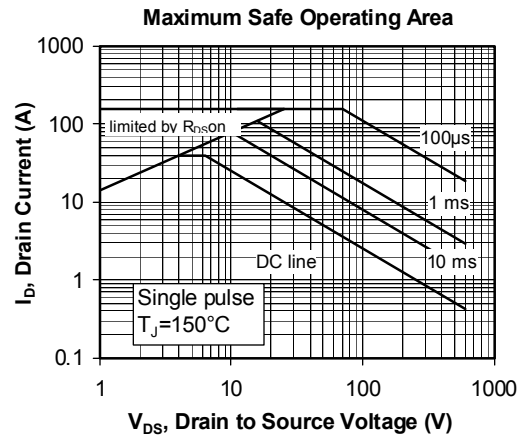
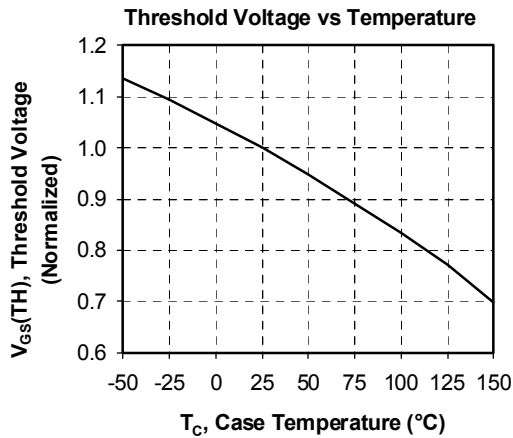
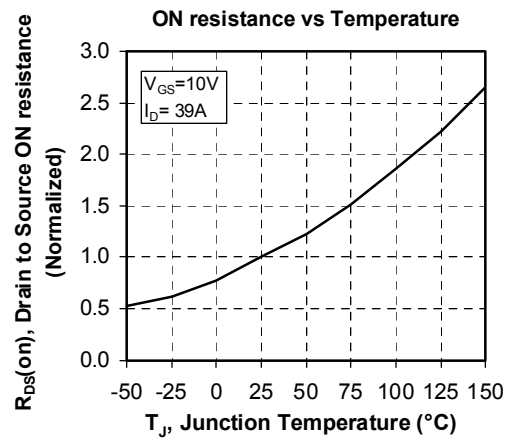
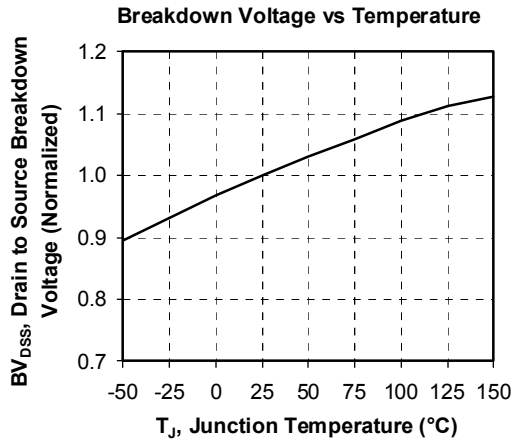
T: Thermistor temperature
R_T: Thermistor value at T

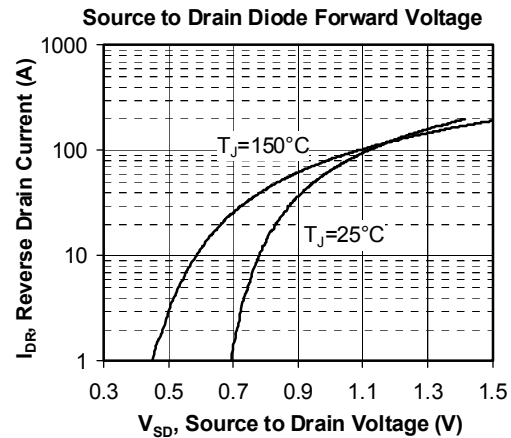
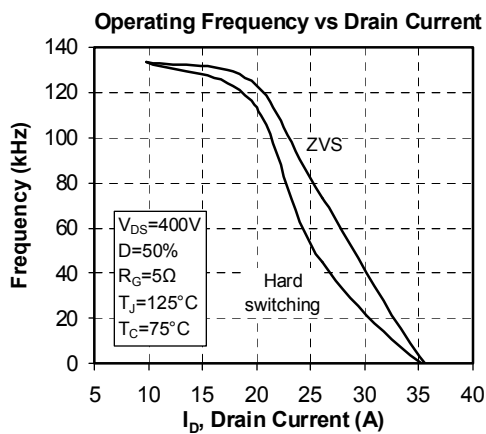
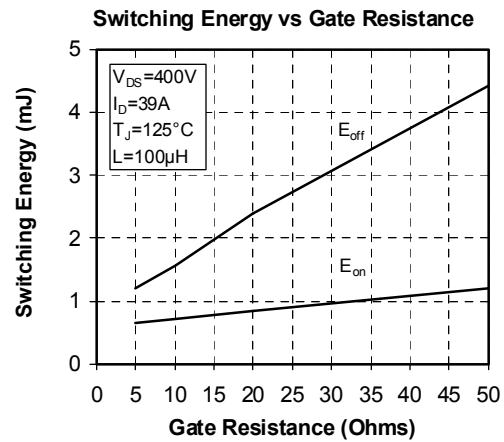
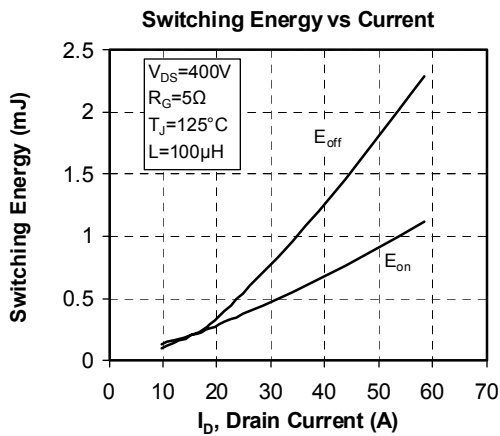
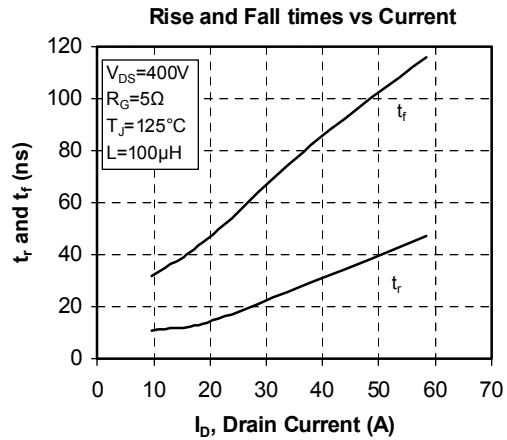
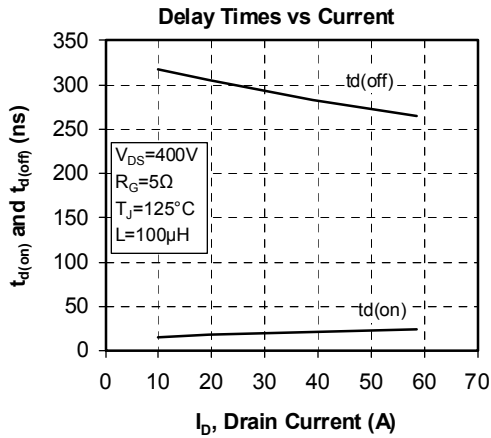
SP4 Package outline (dimensions in mm)



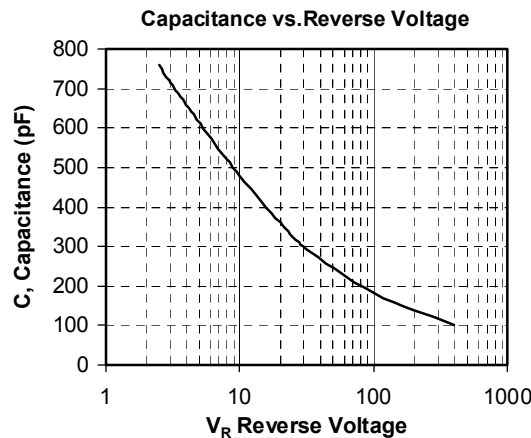
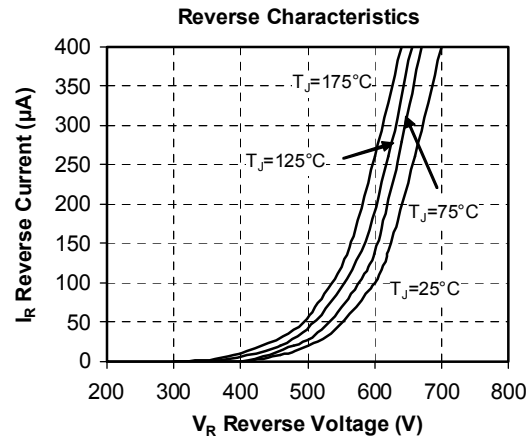
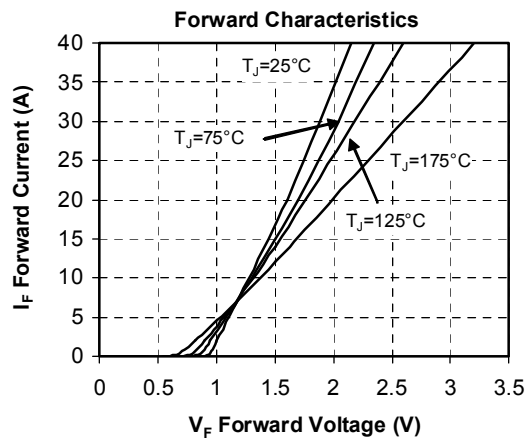
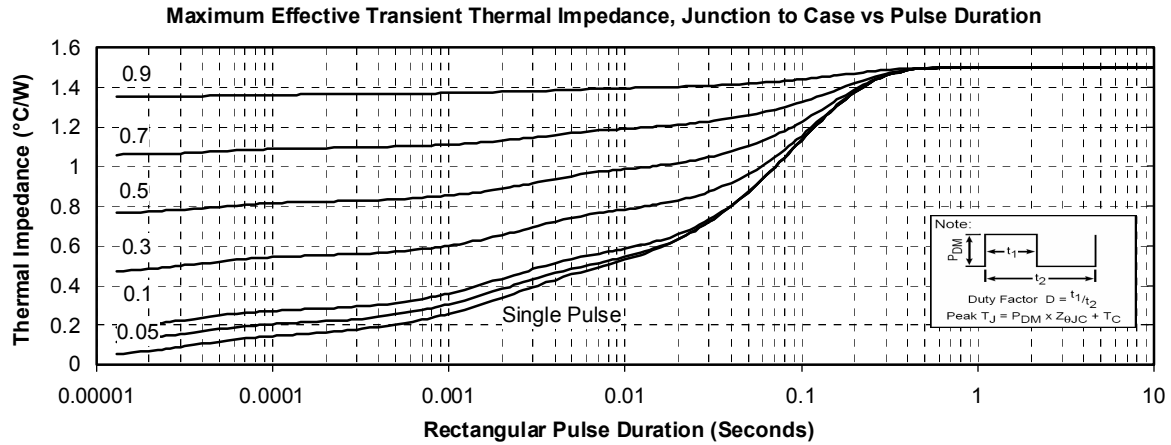
Typical CoolMOS Performance Curve







Typical SiC Diode Performance Curve



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APT's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.